

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company



N-Channel Silicon MOSFET **General-Purpose Switching Device Applications**

Features

- ON-resistance $R_{DS}(on)=0.47\Omega$ (typ.)
- Input capacitance Ciss=1200pF (typ.)

• 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	14	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	9.2	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	52	А
Allowable Power Dissipation	PD		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		106	mJ
Avalanche Current *5	IAV		14	А

*1 Shows chip capability.

*2 Package limited.

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

2SK4087LS-1E

2.54

2.76

1: Gate 2 : Drain 3 : Source

SANYO : TO-220F-3FS

*4 VDD=50V, L=1mH, IAV=14A (Fig.1)

*5 L≤1mH, Single pulse

Package Dimensions

10.16

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Θ

Ó 3.3

Θ

3.68

0.5

15.87

2.98

2 54

unit : mm (typ)

Ø3.18

3.23

1.47 MA



15.8

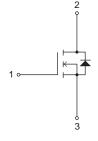
Product & Package Information

- Package : TO-220F-3FS : SC-67
- JEITA. JEDEC
- Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection







41112 TKIM TC-00002744/O1007 TIIM TC-00000930/40407OB TIIM TC-00000630/22107OB TIIM TC-00000371 No. A0555-1/7 O1712 TKIM TC-00002824

Electrical Characteristics at Ta=25°C

Deremeter	Ormshall	0	Ratings				
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =7A	4	8		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=7A, VGS=10V		0.47	0.61	Ω	
Input Capacitance	Ciss			1200		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		220		pF	
Reverse Transfer Capacitance	Crss			50		pF	
Turn-ON Delay Time	t _d (on)			27		ns	
Rise Time	tr			72		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		144		ns	
Fall Time	tf	1		48		ns	
Total Gate Charge	Qg			46		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =14A		8.6		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		26.4		nC	
Diode Forward Voltage	V _{SD}	IS=14A, VGS=0V		0.95	1.3	V	

Fig.1 Unclamped Inductive Switching Test Circuit

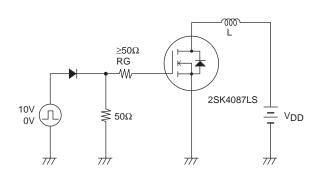
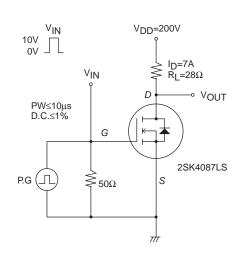
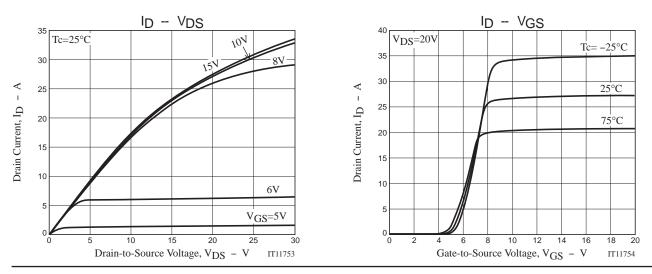


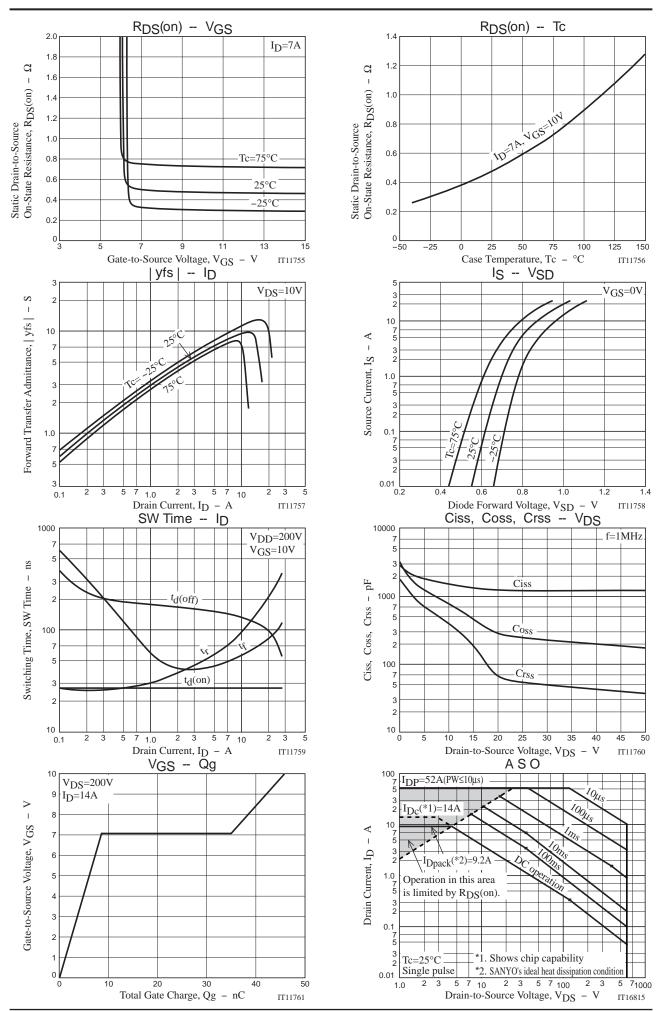
Fig.2 Switching Time Test Circuit

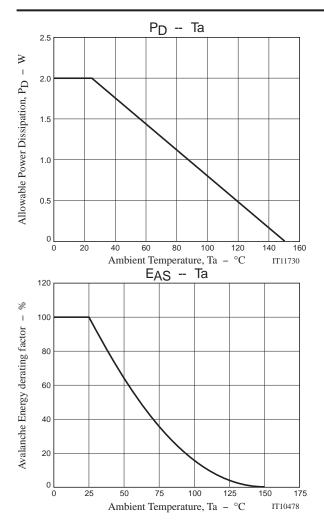


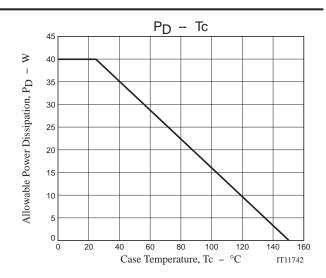
Ordering Information

Device	Device Package		memo	
2SK4087LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free	









Magazine Specification

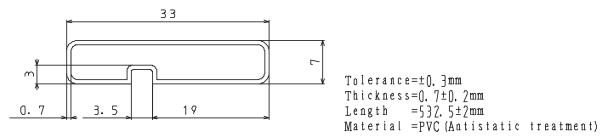
2SK4087LS-1E

1. Packing Format

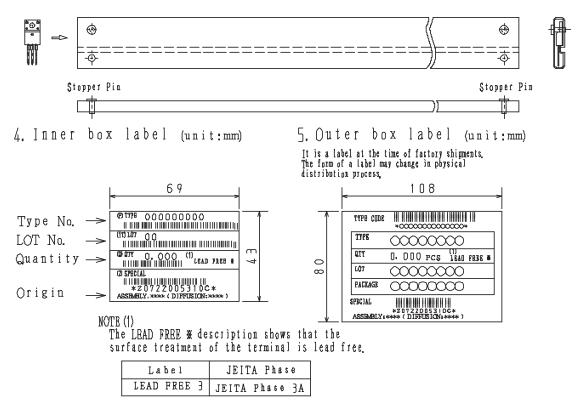
Package Name Magazine Name		Maximum Number of devices contained (pcs)			Packing format		
			Inner box	Quter dax	Inner BOX	Quter BOX	
TO-220F-3F\$	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm {external} 590×225×178	

2. Magazine dimensions (unit:mm)

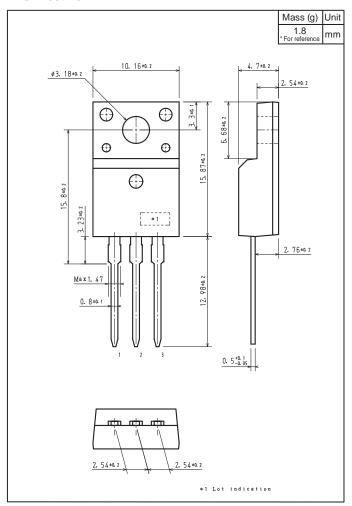
(unit:mm)



3. Storage method to magazine



Outline Drawing 2SK4087LS-1E



Note on usage : Since the 2SK4087LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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